

# MMBT3906LT1

Preferred Device

## General Purpose Transistor

### PNP Silicon

#### Features

- Pb-Free Packages are Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–40	Vdc
Collector–Base Voltage	$V_{CBO}$	–40	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–200	mA <sub>dc</sub>

#### THERMAL CHARACTERISTICS

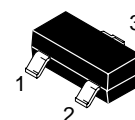
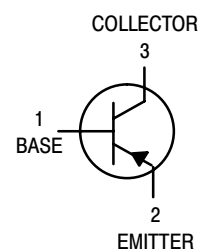
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

- FR–5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



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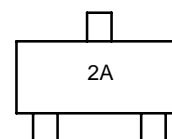
<http://onsemi.com>



SOT–23 (TO–236)  
CASE 318  
Style 6

2A = Specific Device Code

#### MARKING DIAGRAM



#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT3906LT1	SOT–23	3000 / Tape & Reel
MMBT3906LT1G	SOT–23	3000 / Tape & Reel
MMBT3906LT3	SOT–23	10000 / Tape & Reel
MMBT3906LT3G	SOT–23	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# MMBT3906LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage ( $I_C = -1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-40	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = -10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-40	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	—	Vdc
Base Cutoff Current ( $V_{CE} = -30\text{ Vdc}$ , $V_{EB} = -3.0\text{ Vdc}$ )	$I_{BL}$	—	-50	nAdc
Collector Cutoff Current ( $V_{CE} = -30\text{ Vdc}$ , $V_{EB} = -3.0\text{ Vdc}$ )	$I_{CEX}$	—	-50	nAdc

## ON CHARACTERISTICS (Note 3)

DC Current Gain ( $I_C = -0.1\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -50\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -100\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ )	$H_{FE}$	60 80 100 60 30	— — 300 — —	—
Collector–Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -1.0\text{ mA}$ ) ( $I_C = -50\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{CE(sat)}$	— —	-0.25 -0.4	Vdc
Base–Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -1.0\text{ mA}$ ) ( $I_C = -50\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{BE(sat)}$	-0.65 —	-0.85 -0.95	Vdc

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	250	—	MHz
Output Capacitance ( $V_{CB} = -5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	—	4.5	pF
Input Capacitance ( $V_{EB} = -0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	—	10	pF
Input Impedance ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	2.0	12	k $\Omega$
Voltage Feedback Ratio ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	0.1	10	$\times 10^{-4}$
Small–Signal Current Gain ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	100	400	—
Output Admittance ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	3.0	60	$\mu\text{mhos}$
Noise Figure ( $I_C = -100\text{ }\mu\text{A}$ , $V_{CE} = -5.0\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	—	4.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = -3.0\text{ Vdc}$ , $V_{BE} = 0.5\text{ Vdc}$ , $I_C = -10\text{ mA}$ , $I_{B1} = -1.0\text{ mA}$ )	$t_d$	—	35	ns
Rise Time		$t_r$	—	35	
Storage Time	$(V_{CC} = -3.0\text{ Vdc}$ , $I_C = -10\text{ mA}$ , $I_{B1} = I_{B2} = -1.0\text{ mA}$ )	$t_s$	—	225	ns
Fall Time		$t_f$	—	75	

3. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

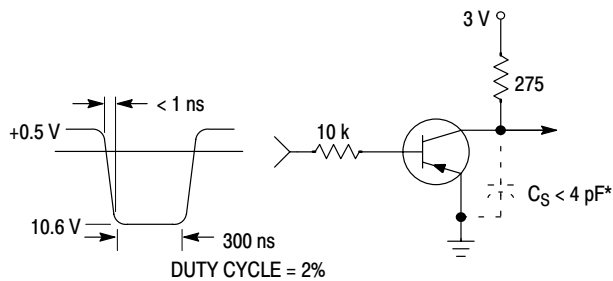


Figure 1. Delay and Rise Time Equivalent Test Circuit

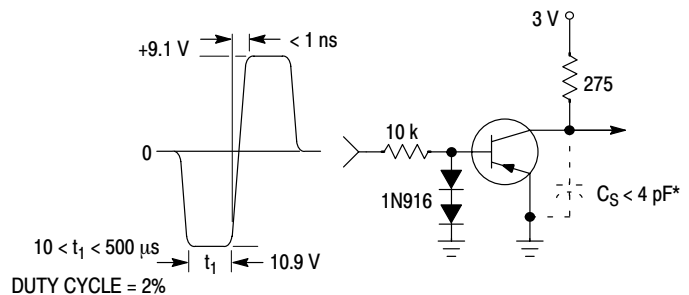


Figure 2. Storage and Fall Time Equivalent Test Circuit

\* Total shunt capacitance of test jig and connectors

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## TYPICAL TRANSIENT CHARACTERISTICS

—  $T_J = 25^\circ\text{C}$   
 - - -  $T_J = 125^\circ\text{C}$

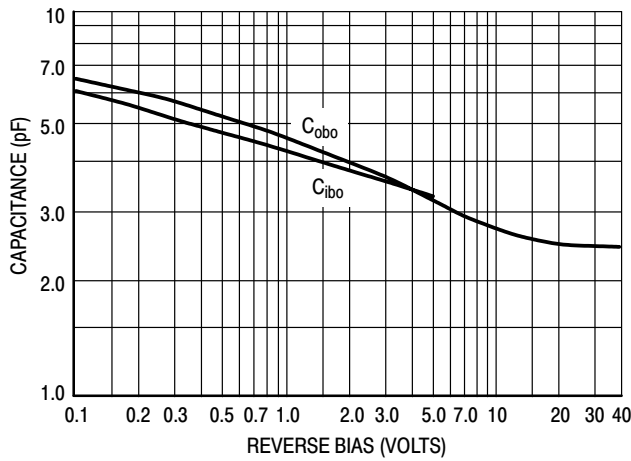


Figure 3. Capacitance

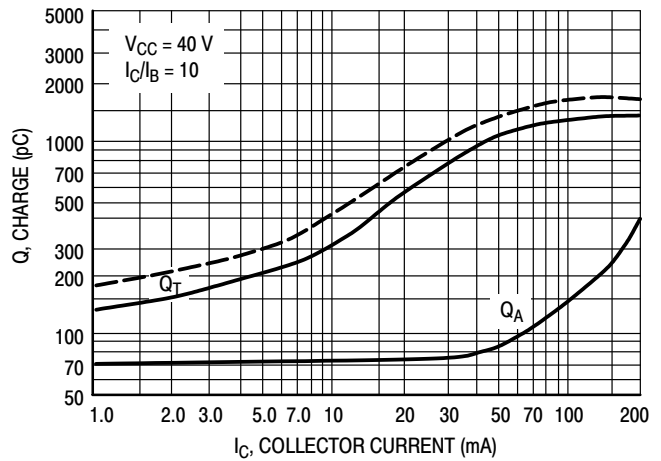


Figure 4. Charge Data

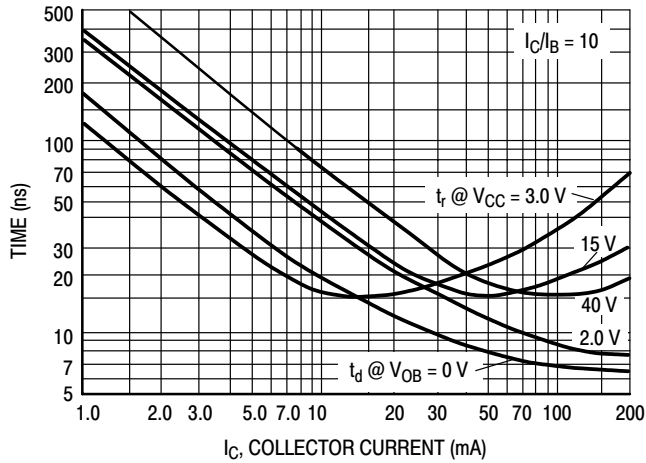


Figure 5. Turn-On Time

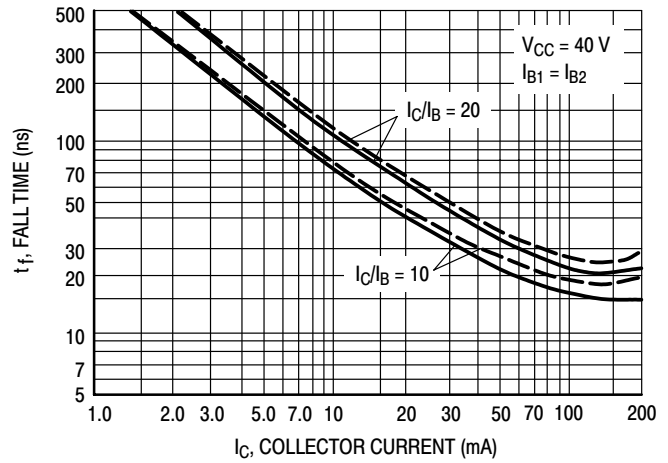


Figure 6. Fall Time

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## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = -5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

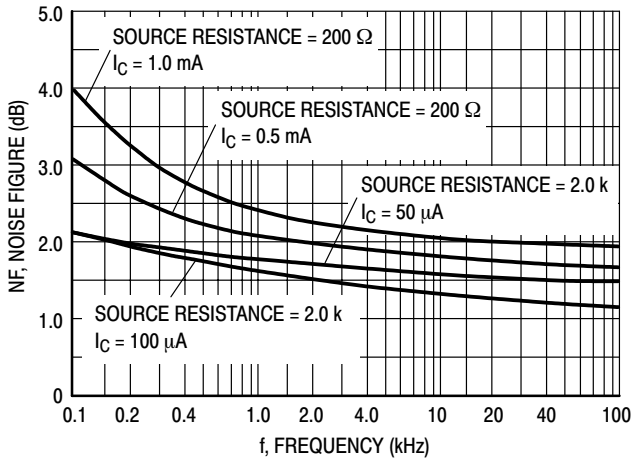


Figure 7.

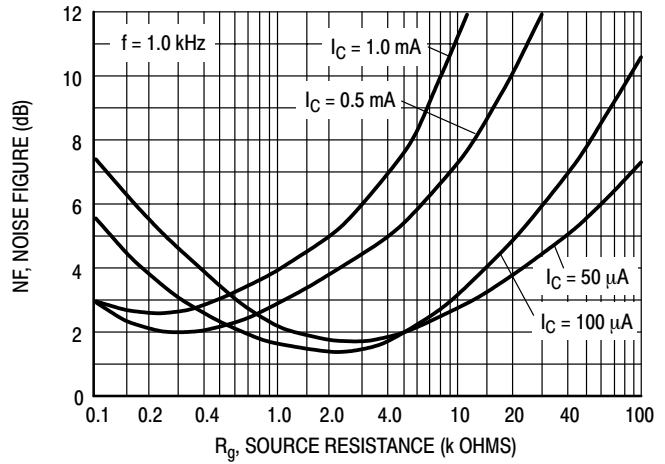


Figure 8.

## h PARAMETERS

( $V_{CE} = -10$  Vdc,  $f = 1.0$  kHz,  $T_A = 25^\circ\text{C}$ )

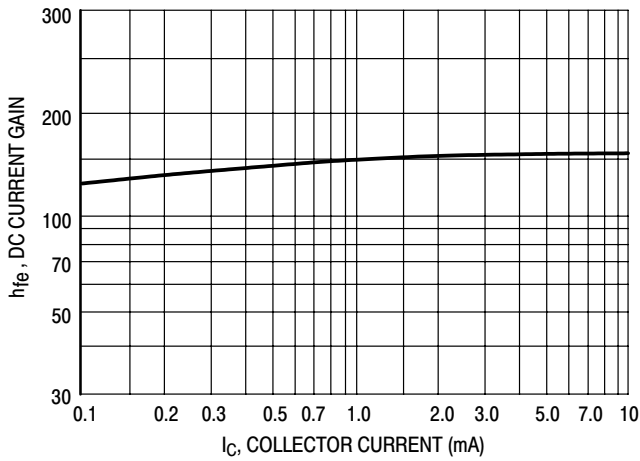


Figure 9. Current Gain

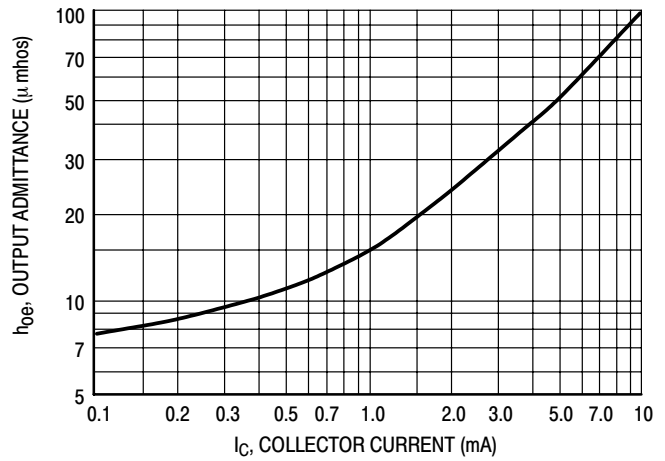


Figure 10. Output Admittance

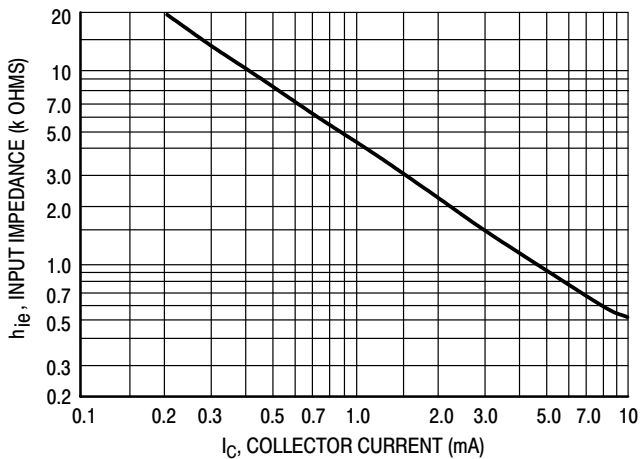


Figure 11. Input Impedance

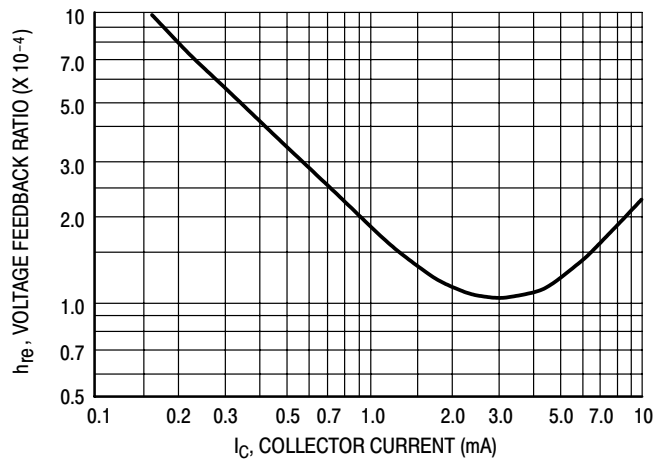


Figure 12. Voltage Feedback Ratio

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## TYPICAL STATIC CHARACTERISTICS

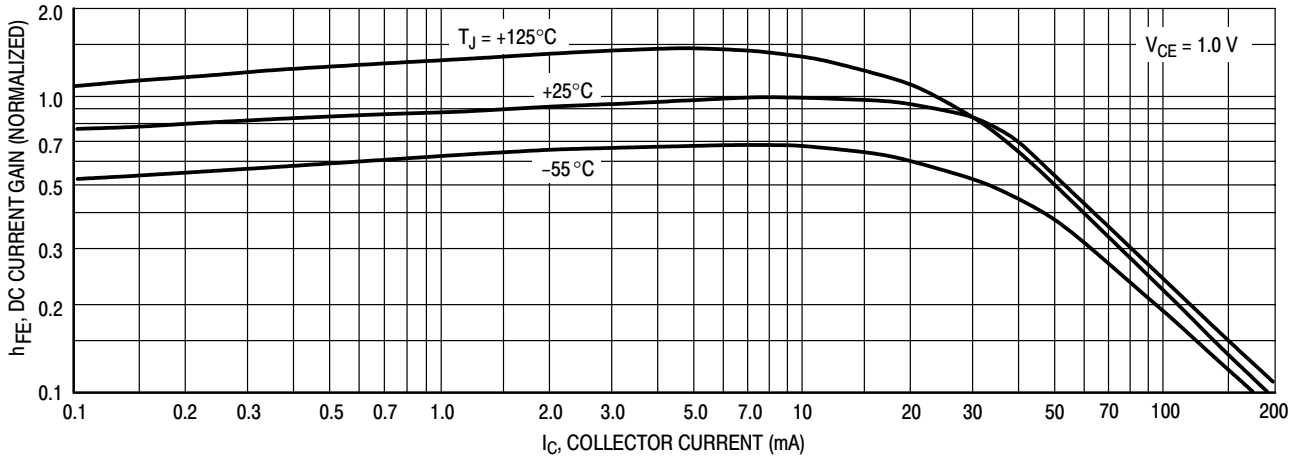


Figure 13. DC Current Gain

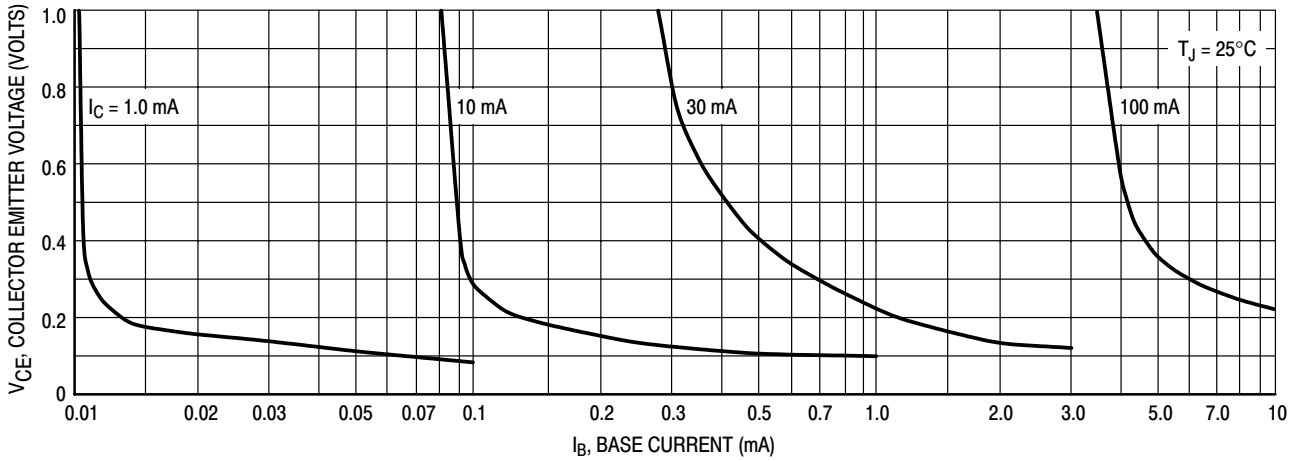


Figure 14. Collector Saturation Region

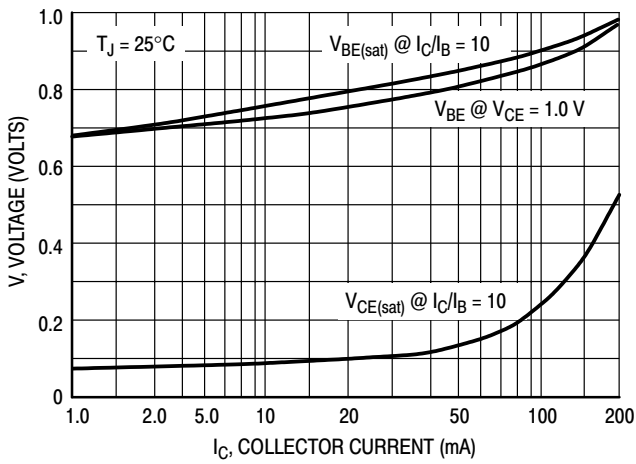


Figure 15. "ON" Voltages

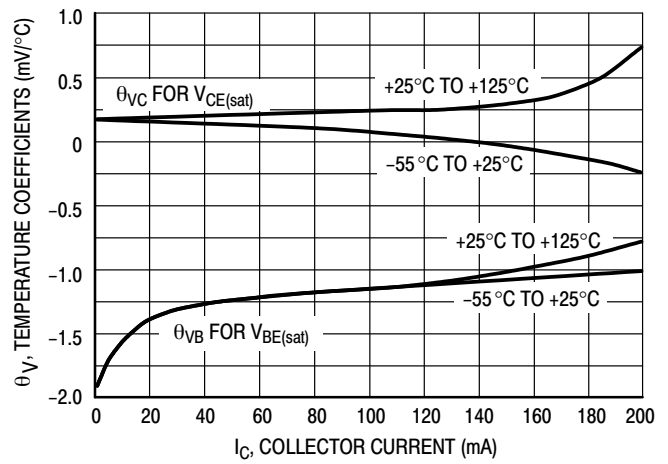


Figure 16. Temperature Coefficients

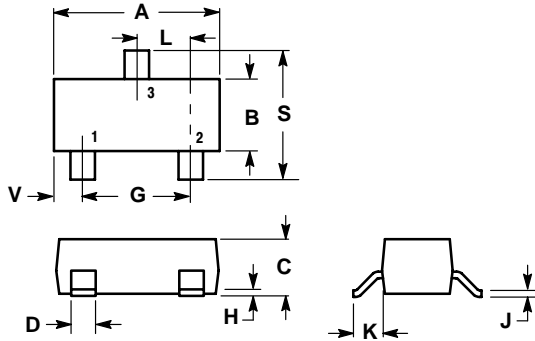
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## PACKAGE DIMENSIONS

### SOT-23 (TO-236) CASE 318-08 ISSUE AH

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
E	0.0701	0.0807	1.78	2.04
F	0.0005	0.0040	0.013	0.100
G	0.0034	0.0070	0.085	0.177
H	0.0140	0.0285	0.35	0.69
I	0.0350	0.0401	0.89	1.02
J	0.0830	0.1039	2.10	2.64
K	0.0177	0.0236	0.45	0.60

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

### SOLDERING FOOTPRINT\*

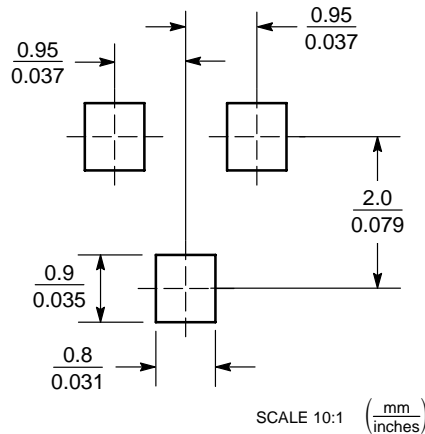


Figure 17. SOT-23

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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